

# FDP7030BLS / FDB7030BLS

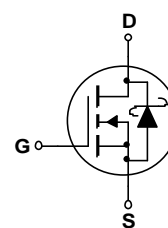
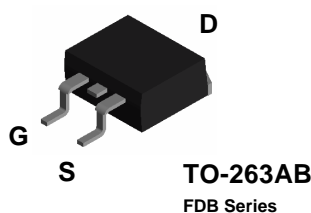
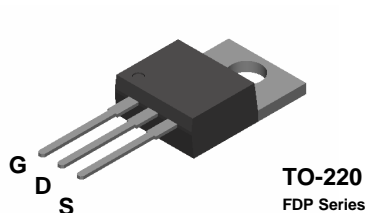
## 30V N-Channel PowerTrench<sup>®</sup> SyncFET™

### General Description

This MOSFET is designed to replace a single MOSFET and parallel Schottky diode in synchronous DC:DC power supplies. This 30V MOSFET is designed to maximize power conversion efficiency, providing a low  $R_{DS(ON)}$  and low gate charge. The FDP7030BLS includes an integrated Schottky diode using Fairchild's monolithic SyncFET technology. The performance of the FDP7030BLS as the low-side switch in a synchronous rectifier is indistinguishable from the performance of the FDP7030BL in parallel with a Schottky diode.

### Features

- 56 A, 30 V.  $R_{DS(ON)} = 10.5 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$   
 $R_{DS(ON)} = 16.5 \text{ m}\Omega @ V_{GS} = 4.5 \text{ V}$
- Includes SyncFET Schottky body diode
- Low gate charge (15nC typical)
- High performance trench technology for extremely low  $R_{DS(ON)}$  and fast switching
- High power and current handling capability



### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-Source Voltage	30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous (Note 1)	56	A
	– Pulsed (Note 1)	160	
$P_D$	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	65	W
	Derate above $25^\circ\text{C}$	0.43	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	$-65$ to $+100$	$^\circ\text{C}$
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	275	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2.3	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	$^\circ\text{C}/\text{W}$

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDB7030BLS	FDB7030BLS	13"	24mm	800 units
FDP7030BLS	FDP7030BLS	Tube	n/a	45

**Electrical Characteristics** $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 10\text{ mA}$ , Referenced to $25^\circ\text{C}$		22		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$			500	$\mu\text{A}$
$I_{GSSF}$	Gate–Body Leakage, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA
$I_{GSSR}$	Gate–Body Leakage, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA
<b>On Characteristics (Note 2)</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 1\text{ mA}$	1	2.3	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 1\text{ mA}$ , Referenced to $25^\circ\text{C}$		-4.4		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = 10\text{ V}, I_D = 28\text{ A}$ $V_{GS} = 4.5\text{ V}, I_D = 23\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 28\text{ A}, T_J = 100^\circ\text{C}$		8.6 13.2 12.4	10.5 16.5 16.5	m $\Omega$
$I_{D(on)}$	On–State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$	50			A
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{ V}, I_D = 28\text{ A}$		47		S
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		1708		pF
$C_{oss}$	Output Capacitance			474		pF
$C_{rss}$	Reverse Transfer Capacitance			134		pF
<b>Switching Characteristics (Note 2)</b>						
$t_{d(on)}$	Turn–On Delay Time	$V_{DS} = 15\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\ \Omega$		11	21	ns
$t_r$	Turn–On Rise Time			8	16	ns
$t_{d(off)}$	Turn–Off Delay Time			30	48	ns
$t_f$	Turn–Off Fall Time			16	29	ns
$Q_g$	Total Gate Charge	$V_{DS} = 15\text{ V}, I_D = 28\text{ A},$ $V_{GS} = 5\text{ V}$		15	21	nC
$Q_{gs}$	Gate–Source Charge			7		nC
$Q_{gd}$	Gate–Drain Charge			5		nC
<b>Drain–Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain–Source Diode Forward Current				3.5	A
$V_{SD}$	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 3.5\text{ A}$ (Note 1) $V_{GS} = 0\text{ V}, I_S = 7\text{ A}$ (Note 1)		0.44 0.60	0.7	V
$t_{rr}$	Diode Reverse Recovery Time	$I_F = 11.5\text{ A},$ $d_I/d_t = 300\text{ A}/\mu\text{s}$ (Note 2)		20		ns
$Q_{rr}$	Diode Reverse Recovery Charge			20		nC

**Notes:**

1. Pulse Test: Pulse Width < 300 $\mu\text{s}$ , Duty Cycle < 2.0%
2. See "SyncFET Schottky body diode characteristics" below.

## Typical Characteristics

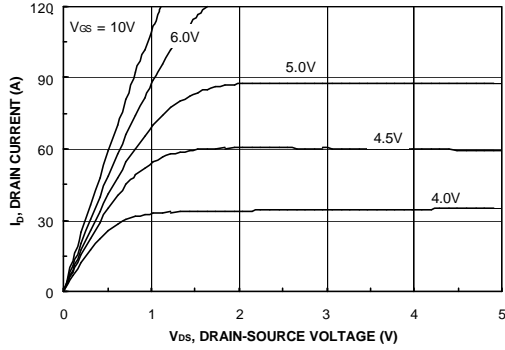


Figure 1. On-Region Characteristics.

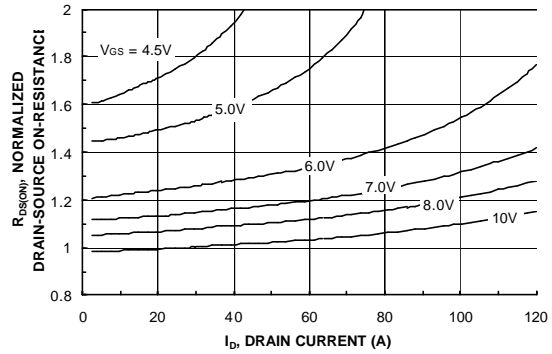


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

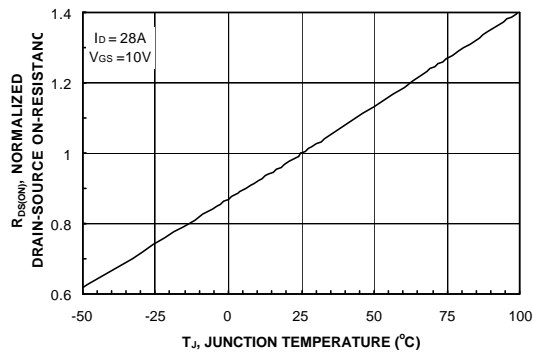


Figure 3. On-Resistance Variation with Temperature.

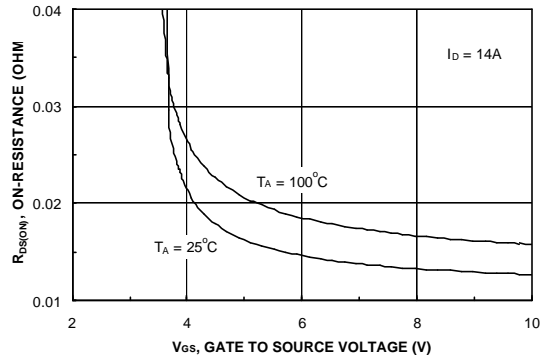


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

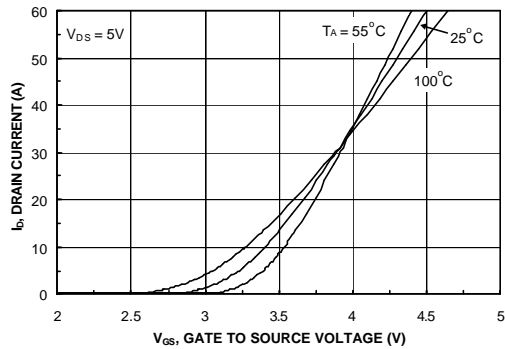


Figure 5. Transfer Characteristics.

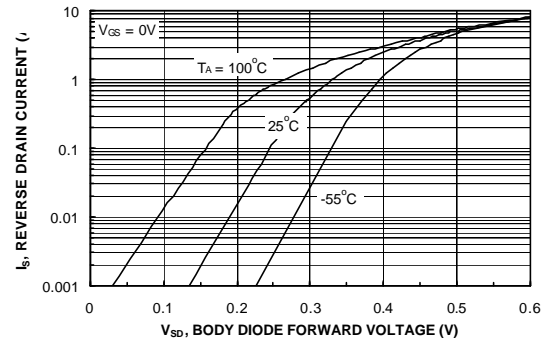
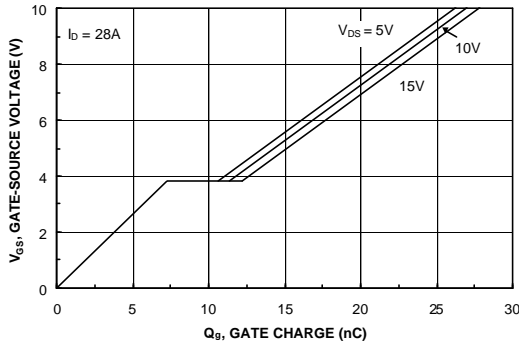
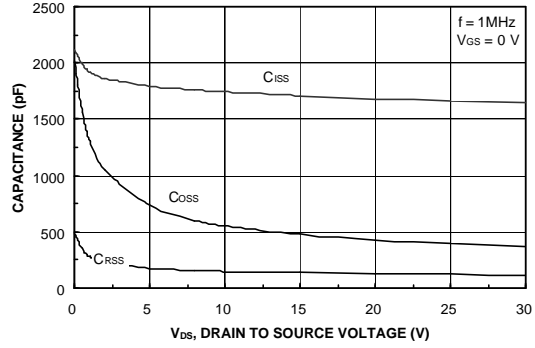


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

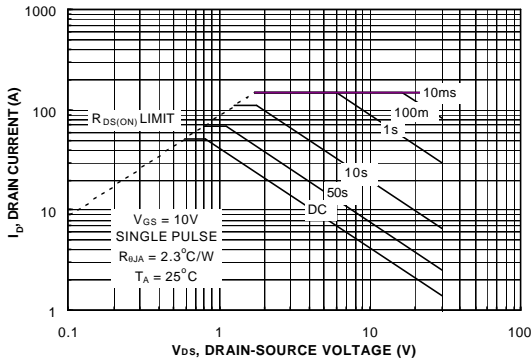
**Typical Characteristics** (continued)



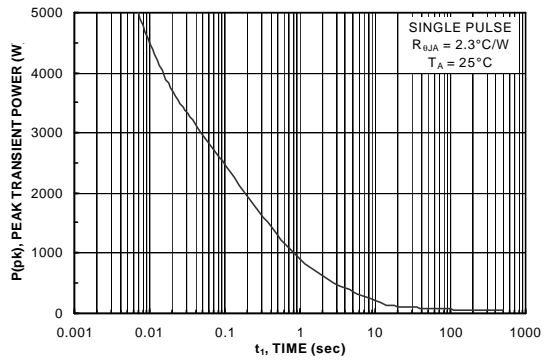
**Figure 7. Gate Charge Characteristics.**



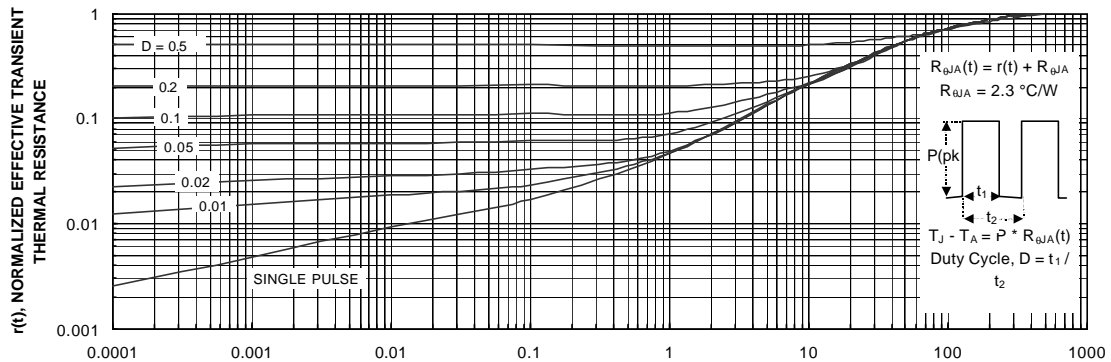
**Figure 8. Capacitance Characteristics.**



**Figure 9. Maximum Safe Operating Area.**



**Figure 10. Single Pulse Maximum Power Dissipation.**

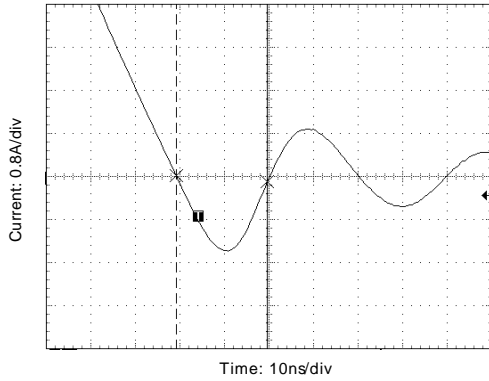


**Figure 11. Transient Thermal Response Curve.**

**Typical Characteristics** (continued)

**SyncFET Schottky Body Diode Characteristics**

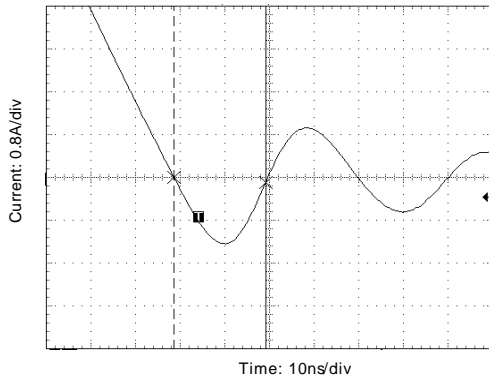
Fairchild's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 12 FDP7030BLS.



**Figure 12. FDP7030BLS SyncFET body diode reverse recovery characteristic.**

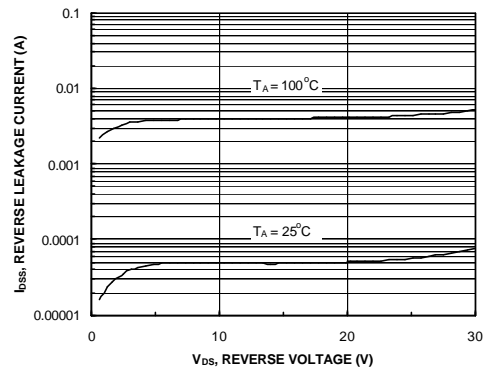
For comparison purposes, Figure 13 shows the reverse recovery characteristics of the body diode of an equivalent size MOSFET produced without SyncFET (FDP7030BL).

**Figure 13. Non-SyncFET (FDP7030BL) body diode reverse recovery characteristic.**



Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

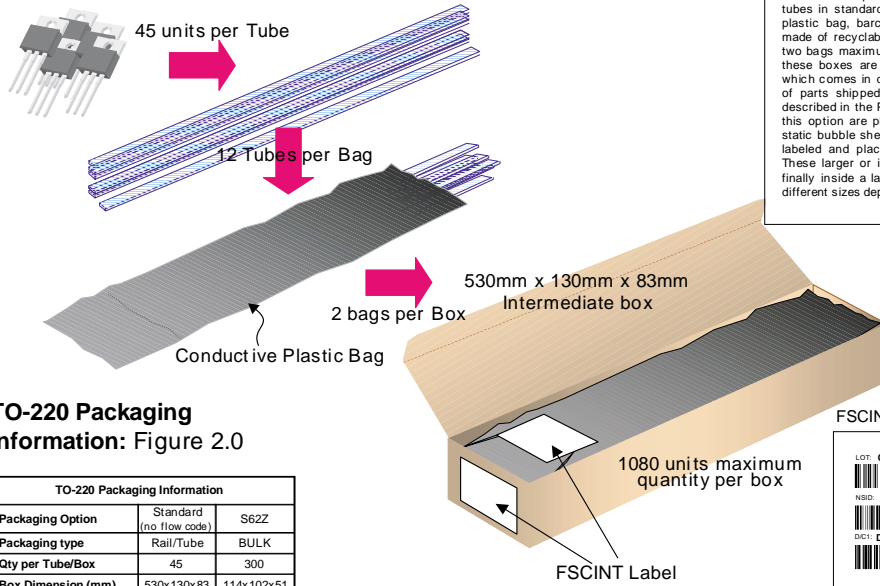
**Figure 14. SyncFET diode reverse leakage versus drain-source voltage and temperature.**



# TO-220 Tube Packing Data



## TO-220 Tube Packing Configuration: Figure 1.0



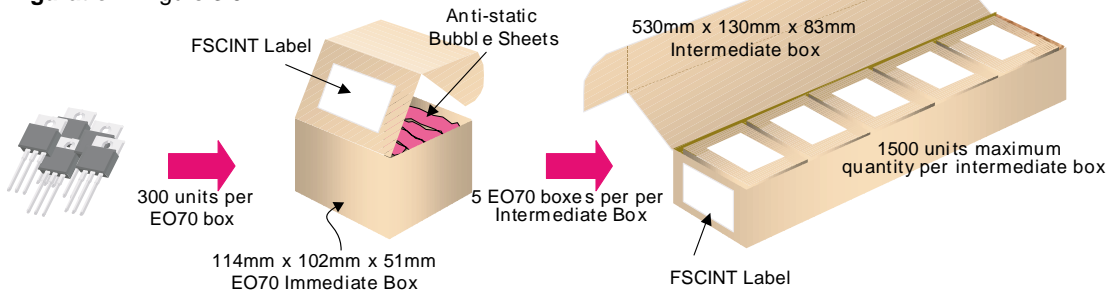
**Packaging Description:**  
 TO-220 parts are shipped normally in tube. The tube is made of PVC plastic treated with anti-static agent. These tubes in standard option are placed inside a dissipative plastic bag, barcode labeled, and placed inside a box made of recyclable corrugated paper. One box contains two bags maximum (see fig. 1.0). And one or several of these boxes are placed inside a labeled shipping box which comes in different sizes depending on the number of parts shipped. The other option comes in bulk as described in the Packaging Information table. The units in this option are placed inside a small box laid with anti-static bubble sheet. These smaller boxes are individually labeled and placed inside a larger box. (See fig. 3.0). These larger or intermediate boxes then will be placed finally inside a labeled shipping box which still comes in different sizes depending on the number of units shipped.

## TO-220 Packaging Information: Figure 2.0

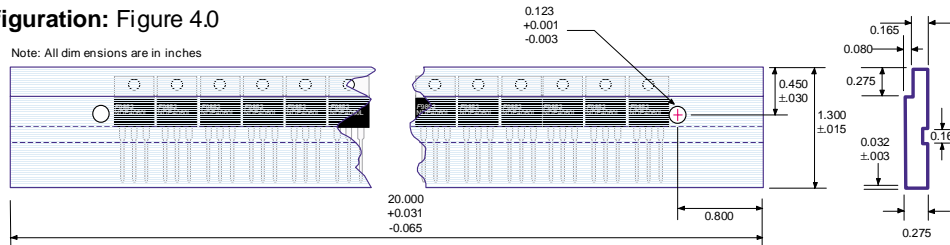
TO-220 Packaging Information		
Packaging Option	Standard (no flow code)	S62Z
Packaging type	Rail/Tube	BULK
Qty per Tube/Box	45	300
Box Dimension (mm)	530x130x83	114x102x51
Max qty per Box	1,080	1,500
Weight per unit (gm)	1.4378	1.4378
Note/Comments		



## TO-220 bulk Packing Configuration: Figure 3.0



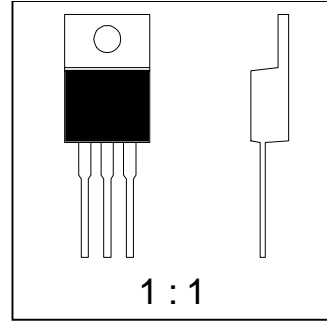
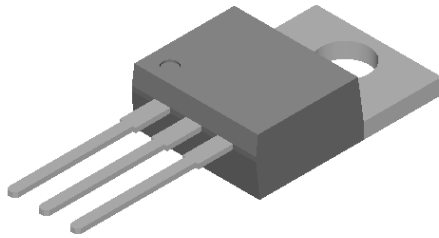
## TO-220 Tube Configuration: Figure 4.0



# TO-220 Package Dimensions

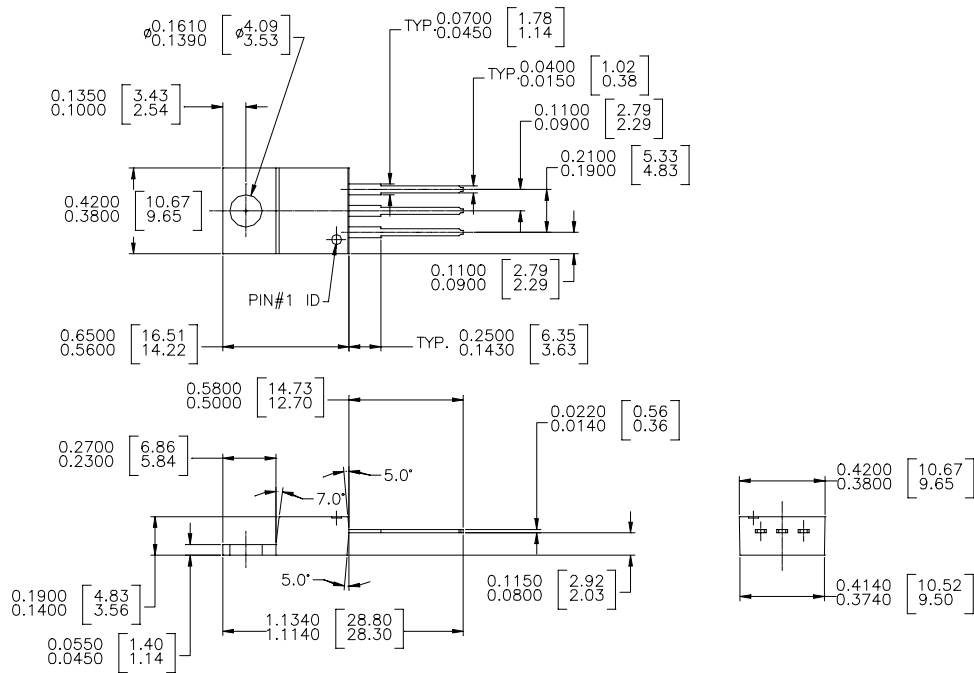


## TO-220 (FS PKG Code 37)



Scale 1:1 on letter size paper  
 Dimensions shown below are in:  
 inches [millimeters]

Part Weight per unit (gram): 1.4378



NOTE : UNLESS OTHERWISE SPECIFIED

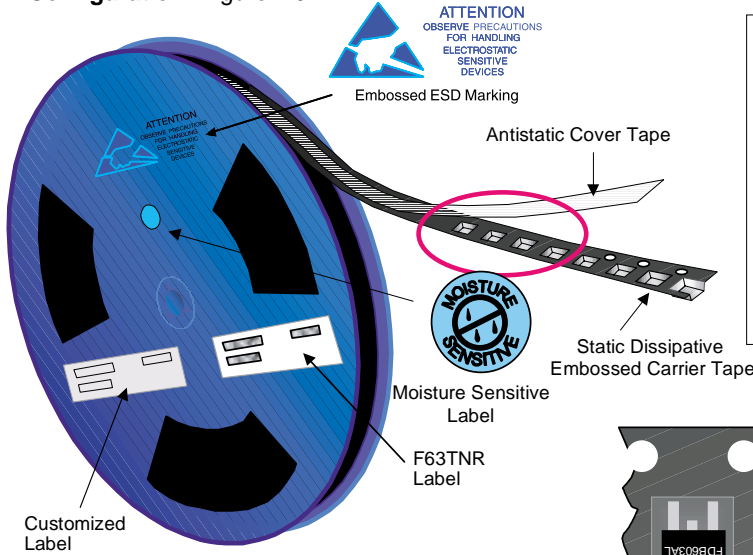
- STANDARD LEAD FINISH :  
 200 MICRONS / 5.08 MICRON MINIMUM  
 LEAD / TIN 15/85 ON OLIN 194 COPPER OR EQUIVALENT
- DIMENSION BASED ON JEDEC STANDARD TO-220  
 VARIATION AB, ISSUE J, DATED 3/24/87

TO 220 3 LEAD

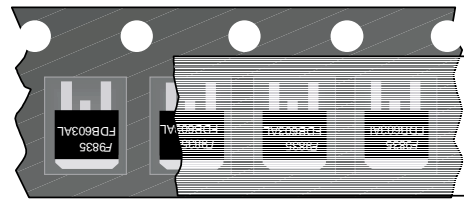
# TO-263AB/D<sup>2</sup>PAK Tape and Reel Data



## TO-263AB/D<sup>2</sup>PAK Packaging Configuration: Figure 1.0

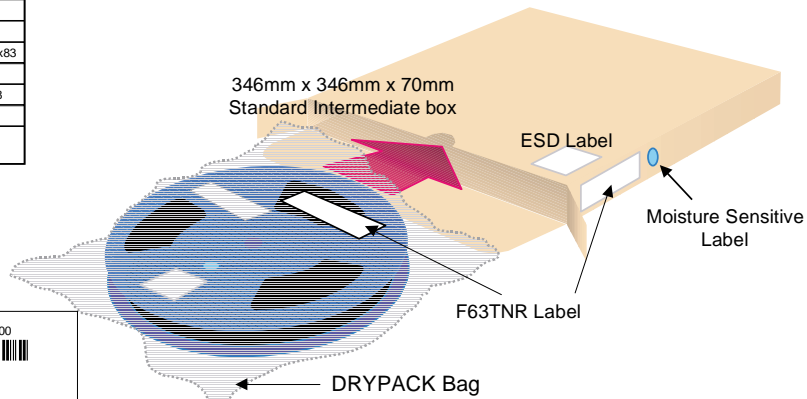


**Packaging Description:**  
 TO-263/D<sup>2</sup>PAK parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 800 units per 13" or 330cm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (anti-static coated). This and some other options are further described in the Packaging Information table.  
 These full reels are individually barcode labeled, dry packed, and placed inside a standard intermediate box (illustrated in figure 1.0) made of recyclable corrugated brown paper. One box contains one reel maximum. And these boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped.

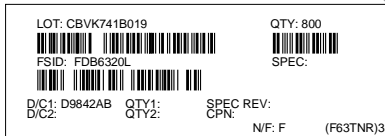


TO-263AB/D<sup>2</sup>PAK Unit Orientation

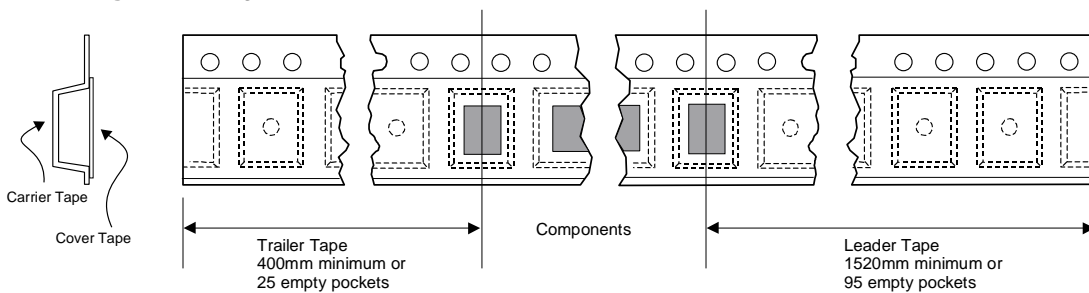
TO-263AB/D <sup>2</sup> PAK Packaging Information		
Packaging Option	Standard (no flow code)	L86Z
Packaging type	TNR	Rail/Tube
Qty per Reel/Tube/Bag	800	45
Reel Size	13" Dia	-
Box Dimension (mm)	346x346x70	530x130x83
Max qty per Box	800	1,080
Weight per unit (gm)	1.4378	1.4378
Weight per Reel	1.6050	-
Note/Comments		



### F63TNR Label sample



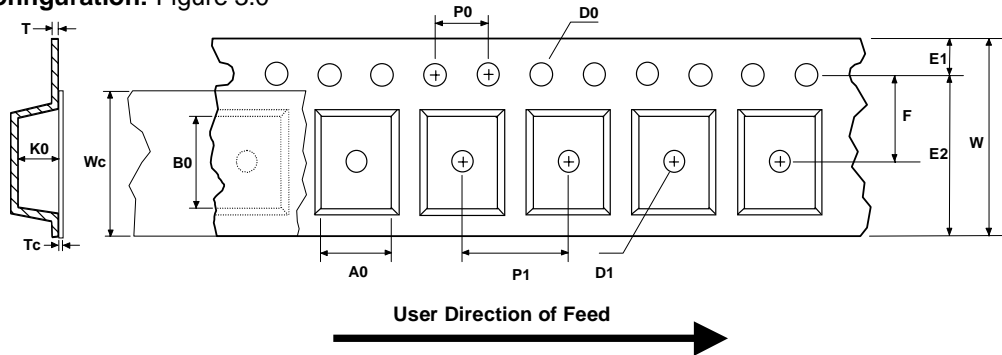
## TO-263AB/D<sup>2</sup>PAK Tape Leader and Trailer Configuration: Figure 2.0





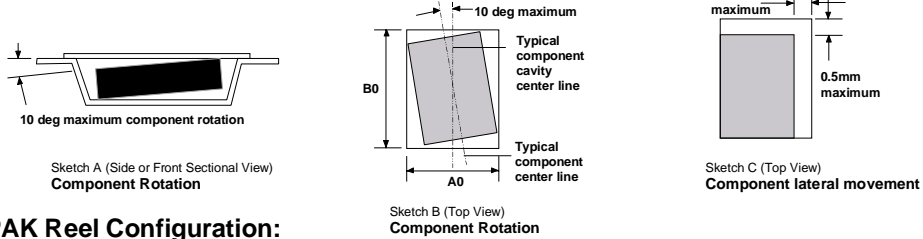
# TO-263AB/D<sup>2</sup>PAK Tape and Reel Data, continued

## TO-263AB/D<sup>2</sup>PAK Embossed Carrier Tape Configuration: Figure 3.0

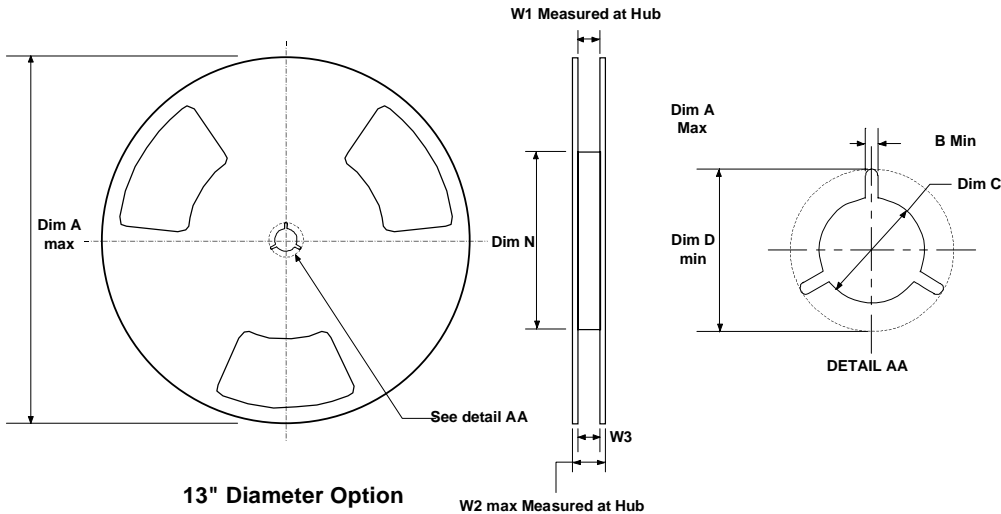


Dimensions are in millimeter														
Pkg type	A0	B0	W	D0	D1	E1	E2	F	P1	P0	K0	T	Wc	Tc
TO263AB/ D <sup>2</sup> PAK (24mm)	10.60 +/-0.10	16.70 +/-0.20	24.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	22.25 min	11.50 +/-0.10	16.0 +/-0.1	4.0 +/-0.1	4.90 +/-0.10	0.450 +/-0.150	21.0 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



## TO-263AB/D<sup>2</sup>PAK Reel Configuration: Figure 4.0

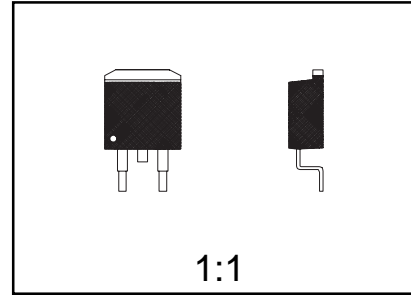
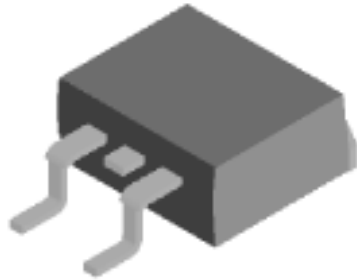


Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
24mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.961 +0.078/-0.000 24.4 +2/0	1.197 30.4	0.941 - 0.1.079 23.9 - 27.4

# TO-263AB/D<sup>2</sup>PAK Package Dimensions



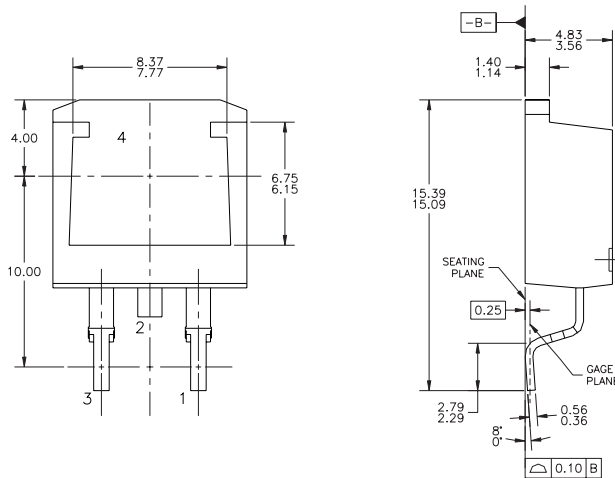
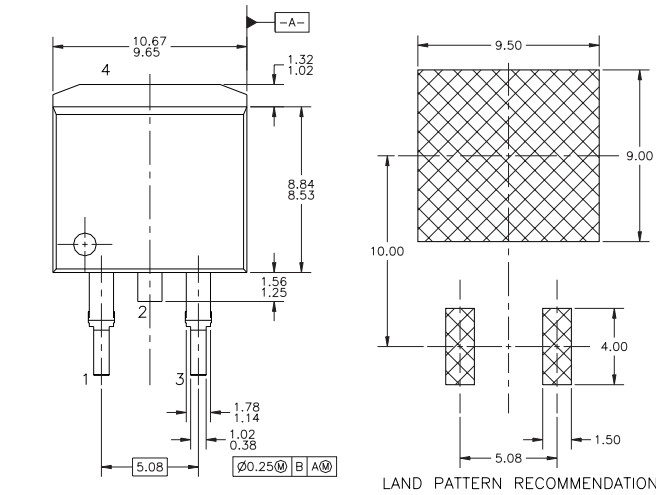
## TO-263AB/D<sup>2</sup>PAK (FS PKG Code 45)



Scale 1:1 on letter size paper

Dimensions shown below are in:  
inches [millimeters]

Part Weight per unit (gram): 1.4378



- NOTES: UNLESS OTHERWISE SPECIFIED  
 A) ALL DIMENSIONS ARE IN MILLIMETERS.  
 B) STANDARD LEAD FINISH:  
 200 MICROINCHES / 5.08 MICROMETERS MIN.  
 LEAD/TIN 15/85 ON OLIN 194 COPPER OR  
 EQUIVALENT.  
 C) MAXIMUM VERTICAL BURR ON HEATSINK NOT  
 TO EXCEED 0.003 INCH / 0.05mm.  
 D) NO PACKAGE CHIPS, CRACKS OR SURFACE  
 IDENTIFICATION ALLOWED AFTER FORMING.  
 E) REFERENCE JEDEC, TO-263, ISSUE C,  
 VARIATION AB, DATED 2/92.

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Bottomless <sup>TM</sup>	FAST <sub>r</sub> <sup>TM</sup>	PACMAN <sup>TM</sup>	SuperSOT <sup>TM</sup> -6
CoolFET <sup>TM</sup>	FRFET <sup>TM</sup>	POP <sup>TM</sup>	SuperSOT <sup>TM</sup> -8
CROSSVOLT <sup>TM</sup>	GlobalOptoisolator <sup>TM</sup>	PowerTrench <sup>®</sup>	SyncFET <sup>TM</sup>
DenseTrench <sup>TM</sup>	GTO <sup>TM</sup>	QFET <sup>TM</sup>	TinyLogic <sup>TM</sup>
DOMET <sup>TM</sup>	HiSeC <sup>TM</sup>	QS <sup>TM</sup>	UHC <sup>TM</sup>
EcoSPARK <sup>TM</sup>	ISOPLANAR <sup>TM</sup>	QT Optoelectronics <sup>TM</sup>	UltraFET <sup>®</sup>
E <sup>2</sup> CMOS <sup>TM</sup>	LittleFET <sup>TM</sup>	Quiet Series <sup>TM</sup>	VCX <sup>TM</sup>
EnSigna <sup>TM</sup>	MicroFET <sup>TM</sup>	SILENT SWITCHER <sup>®</sup>	
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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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### Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.